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# FGL40N120AND 1200V NPT IGBT

### **Features**

· High speed switching

• Low saturation voltage :  $V_{CE(sat)} = 2.6 \text{ V} @ I_C = 40 \text{A}$ 

· High input impedance

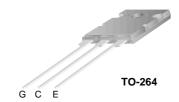
• CO-PAK, IGBT with FRD :  $t_{rr} = 75$ ns (typ.)

### **Applications**

Induction Heating, UPS, AC & DC motor controls and general purpose inverters.

### **Description**

Employing NPT technology, Fairchild's AND series of IGBTs provides low conduction and switching losses. The AND series offers an solution for application such as induction heating (IH), motor control, general purpose inverters and uninterruptible power supplies (UPS).





### **Absolute Maximum Ratings**

Symbol	Parameter		FGL40N120AND	Units
V <sub>CES</sub>	Collector-Emitter Voltage		1200	V
$V_{GES}$	Gate-Emitter Voltage		±25	V
	Collector Current	@T <sub>C</sub> = 25°C	64	Α
IC	Collector Current	@T <sub>C</sub> = 100°C	40	Α
I <sub>CM(1)</sub>	Pulsed Collector Current		160	Α
I <sub>F</sub>	Diode Continuous Forward Current @T <sub>C</sub> = 100°C		40	Α
I <sub>FM</sub>	Diode Maximum Forward Current		240	Α
D	Maximum Power Dissipation	@T <sub>C</sub> = 25°C	500	W
$P_{D}$	Maximum Power Dissipation	@T <sub>C</sub> = 100°C	200	W
SCWT	Short Circuit Withstand Time, V <sub>CE</sub> = 600V, V <sub>GE</sub> = 15V, T <sub>C</sub> = 125°C		10	μs
TJ	Operating Junction Temperature		-55 to +150	°C
T <sub>STG</sub>	Storage Temperature Range		-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 seconds		300	°C

#### Notes:

(1) Pulse width limited by max. junction temperature

### **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance, Junction-to-Case		0.25	°C/W
$R_{\theta JC}(DIODE)$	Thermal Resistance, Junction-to-Case		0.7	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient		25	°C/W

# **Package Marking and Ordering Information**

<b>Device Marking</b>	Device	Package	Reel Size	Tape Width	Quantity
FGL40N120AND	FGL40N120AND	TO-264	=	-	25

# Electrical Characteristics of the IGBT $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
Off Charact	eristics					
BV <sub>CES</sub>	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V$ , $I_C = 1mA$	1200			V
BV <sub>CES</sub> / ΔT <sub>J</sub>	Temperature Coefficient of Breakdown Voltage	V <sub>GE</sub> = 0V, I <sub>C</sub> = 1mA		0.6		V/°C
I <sub>CES</sub>	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$			1	mA
I <sub>GES</sub>	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$			±250	nA
On Charact	eristics					
V <sub>GE(th)</sub>	G-E Threshold Voltage	$I_{C} = 250 \mu A, V_{CE} = V_{GE}$	3.5	5.5	7.5	V
- GE(III)		I <sub>C</sub> = 40A, V <sub>GE</sub> = 15V		2.6	3.2	V
V <sub>CE(sat)</sub>	Collector to Emitter Saturation Voltage	I <sub>C</sub> = 40A, V <sub>GE</sub> = 15V, T <sub>C</sub> = 125°C		2.9		V
		I <sub>C</sub> = 64A, V <sub>GE</sub> = 15V		3.15		V
Dynamic Cl	haracteristics			l .		1
C <sub>ies</sub>	Input Capacitance			3200		pF
C <sub>oes</sub>	Output Capacitance	$V_{CE} = 30V, V_{GE} = 0V$		370		pF
C <sub>res</sub>	Reverse Transfer Capacitance	f = 1MHz		125		pF
Switching (	Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time			15		ns
t <sub>r</sub>	Rise Time	]		20		ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{CC} = 600V, I_{C} = 40A,$		110		ns
t <sub>f</sub>	Fall Time	$R_G = 5\Omega, V_{GE} = 15V,$		40	80	ns
E <sub>on</sub>	Turn-On Switching Loss	Inductive Load, T <sub>C</sub> = 25°C		2.3	3.45	mJ
E <sub>off</sub>	Turn-Off Switching Loss			1.1	1.65	mJ
E <sub>ts</sub>	Total Switching Loss			3.4	5.1	mJ
t <sub>d(on)</sub>	Turn-On Delay Time			20		ns
t <sub>r</sub>	Rise Time			25		ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{CC} = 600V, I_{C} = 40A,$		120		ns
t <sub>f</sub>	Fall Time	$R_G = 5\Omega$ , $V_{GE} = 15V$ ,		45		ns
E <sub>on</sub>	Turn-On Switching Loss	Inductive Load, T <sub>C</sub> = 125°C		2.5		mJ
E <sub>off</sub>	Turn-Off Switching Loss			1.8		mJ
E <sub>ts</sub>	Total Switching Loss			4.3		mJ
Qg	Total Gate charge			220	330	nC
Q <sub>ge</sub>	Gate-Emitter Charge	$V_{CE} = 600V, I_{C} = 40A,$ $V_{GE} = 15V$		25	38	nC
Q <sub>gc</sub>	Gate-Collector Charge	1 *GE = 10 *		130	195	nC

# Electrical Characteristics of DIODE $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Units
V	Diode Forward Voltage	I <sub>F</sub> = 40A	T <sub>C</sub> = 25°C		3.2	4.0	V
$V_{FM}$			T <sub>C</sub> = 125°C		2.7		V
+	Diode Reverse Recovery Time		T <sub>C</sub> = 25°C		75	112	nS
t <sub>rr</sub>	Diode Reverse Recovery Time		T <sub>C</sub> = 125°C		130		113
	Diode Peak Reverse Recovery	I <sub>F</sub> = 40A,	T <sub>C</sub> = 25°C		8	12	Α
l rr	Current		T <sub>C</sub> = 125°C		13		_ ^
Q <sub>rr</sub>	Diode Reverse Recovery Charge		T <sub>C</sub> = 25°C		300	450	nC
			T <sub>C</sub> = 125°C		845		iiC

### **Typical Performance Characteristics**

**Figure 1. Typical Output Characteristics** 

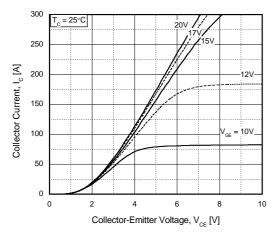


Figure 3. Saturation Voltage vs. Case
Temperature at Variant Current Level

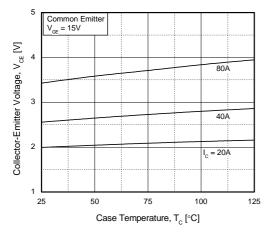


Figure 5. Saturation Voltage vs. V<sub>GE</sub>

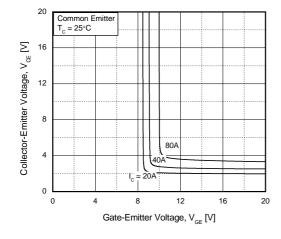


Figure 2. Typical Saturation Voltage Characteristics

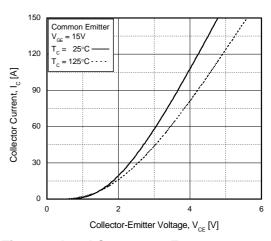


Figure 4. Load Current vs. Frequency

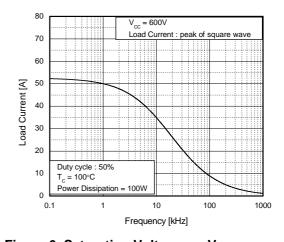
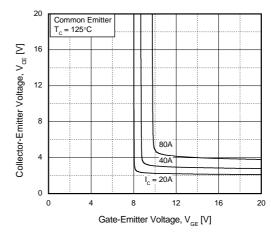


Figure 6. Saturation Voltage vs.  $V_{\text{GE}}$ 



### Typical Performance Characteristics (Continued)

Figure 7. Capacitance Characteristics

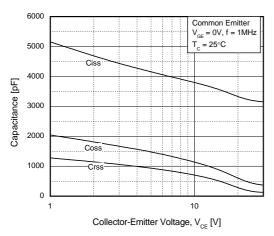


Figure 9. Turn-Off Characteristics vs. **Gate Resistance** 

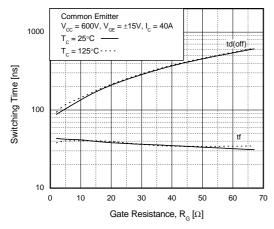


Figure 11. Turn-On Characteristics vs. **Collector Current** 

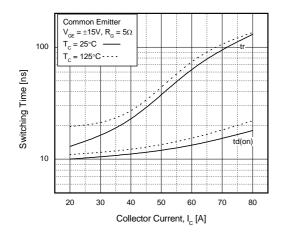


Figure 8. Turn-On Characteristics vs. Gate Resistance

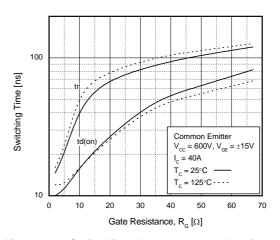


Figure 10. Switching Loss vs. Gate Resistance

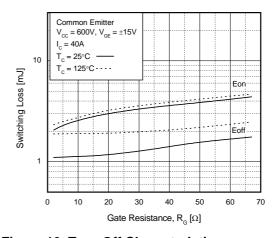
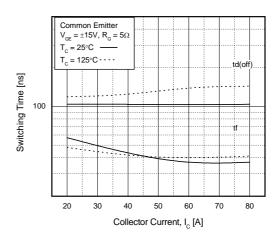


Figure 12. Turn-Off Characteristics vs. **Collector Current** 



### Typical Performance Characteristics (Continued)

Figure 13. Switching Loss vs. Collector Current

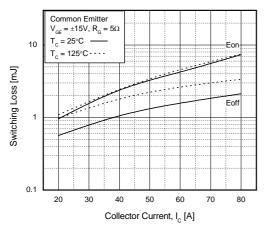


Figure 15. SOA Characteristics

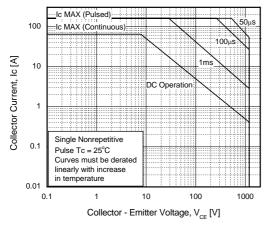


Figure 17. Forward Characteristics

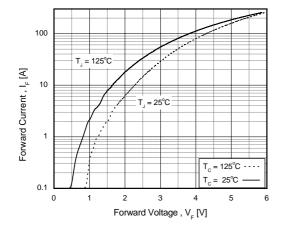


Figure 14. Gate Charge Characteristics

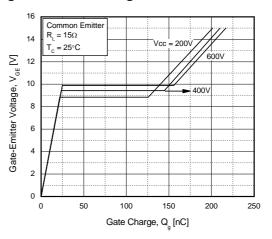


Figure 16. Turn-Off SOA

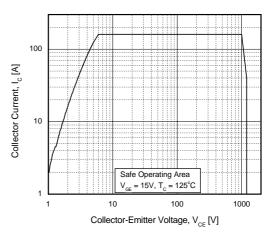
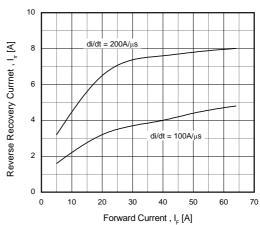


Figure 18. Reverse Recovery Current



### Typical Performance Characteristics (Continued)

Figure 19. Stored Charge

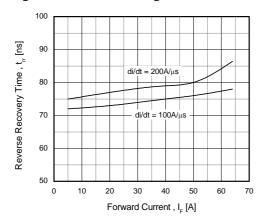


Figure 20. Reverse Recovery Time

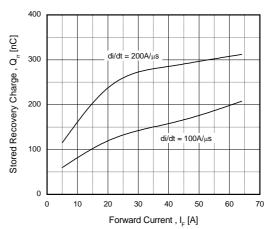
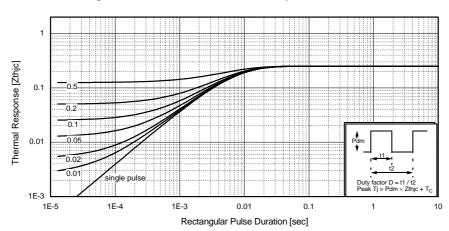
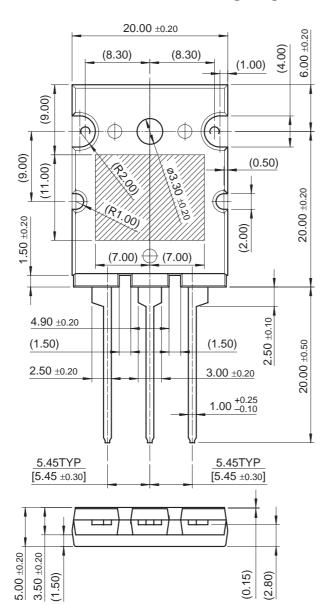


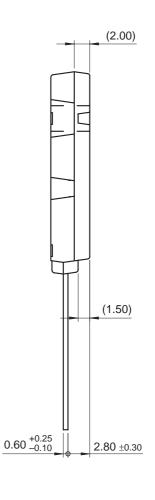
Figure 21. Transient Thermal Impedance of IGBT



### **Mechanical Dimensions**

TO-264





Dimensions in Millimeters





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